1. Title:	EUV-Reflectometer for EUV Lithography
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3. Abstract body:

Research and development efforts on EUV technology for the 32 nm node and beyond are progressing rapidly. Although a big concern is defect control in EUV mask blanks, development of mask-making process will be an important factor in acceptance of this technology. A reflectometer for mask blank and EUVL mask has been installed in April 2006 for qualify check of EUV mask blank and EUV mask at samsung.

In this paper, we report on the results of an installation and evaluation where the EUV reflectometer is used to qualify the mask making process. Additionally, the identified demands for EUV technology for future metrology, high throughput, small measurement spot, low repeatability error and calibration error will be discussed.

Keywords: EUV masks, Mask blank, Reflectometer,